

## G2N4401

### NPN EPITAXIAL PLANAR TRANSISTOR

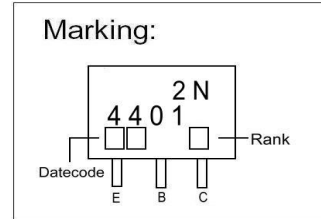
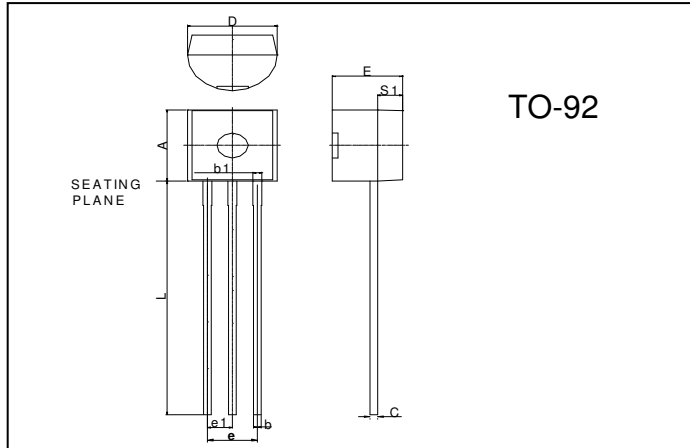
#### Description

The G2N4401 is designed for general purpose switching and amplifier applications.

#### Features

- \*Complementary to G2N4403
- \*High Power Dissipation: 625mW at 25°C
- \*High DC Current Gain: 100-300 at 150mA
- \*High Breakdown Voltage: 40V Min

#### Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	40	V
Emitter to Base Voltage	VEBO	5	V
Collector Current	IC	600	mA
Total Power Dissipation	PD	625	mW

#### Characteristics at Ta = 25°C

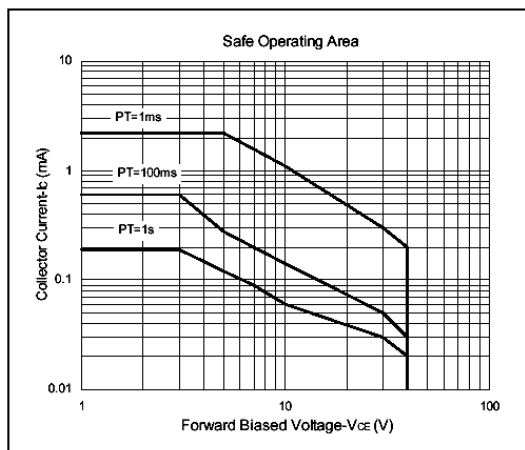
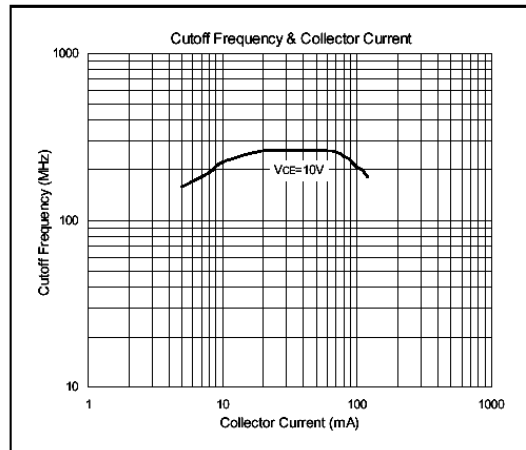
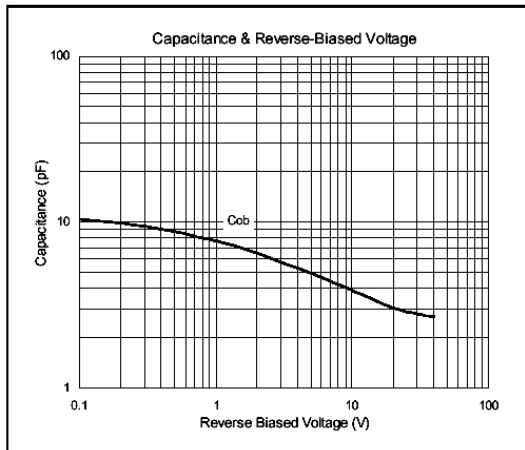
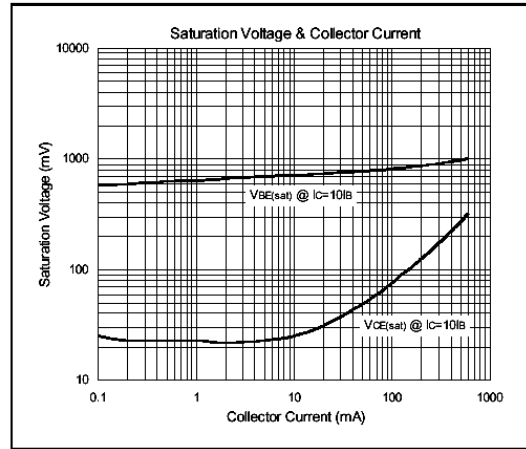
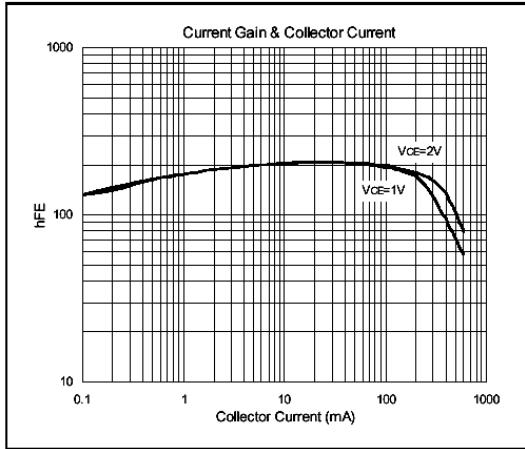
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	IC=100uA
BVCEO	40	-	-	V	IC=1mA
BVEBO	5	-	-	V	IE=10uA
ICEX	-	-	100	nA	VCE=35V, VBE= 0.4V
*VCE(sat)1	-	-	400	mV	IC=150mA, IB=15mA
*VCE(sat)2	-	-	750	mV	IC=500mA, IB=50mA
*VBE(sat)1	750	-	950	mV	IC=150mA, IB=15mA
*VBE(sat)2	-	-	1.2	V	IC=500mA, IB=50mA
*hFE1	20	-	-		VCE=1V, IB=0.1mA
*hFE2	40	-	-		VCE=1V, IC=1mA
*hFE3	80	-	-		VCE=1V, IC=10mA
*hFE4	100	-	300		VCE=1V, IC=150mA
*hFE5	40	-	-		VCE=2V, IC=500mA
fT	250	-	-	MHz	VCE=10V, IC=20mA, f=100MHz
Cob	-	-	6.5	pF	VCB=5V, f=1MHz

#### Classification Of hFE4

Rank	A	B
Range	100-210	190-300

\* Pulse Test: Pulse Width ≤ 380us, Duty Cycle ≤ 2%

## Characteristics Curve



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